

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claim 1 (Currently amended): A method of manufacturing a TFT array panel of a liquid crystal display, said method comprising the steps of:
forming a substrate, a transparent conducting metal layer being formed on the substrate, and then ~~the a~~ first masking process being processing for defining at least a gate electrode, a storage capacitor electrode, and a transparent conducting electrode;
forming a first metal wiring layer by using a selective deposition method for implementing ~~the a~~ wiring layout of the gate electrode, the storage capacitor electrode, a dielectric layer, an A-Si layer, and a poly-Si layer being deposited in order;
processing ~~the a~~ second masking process to form ~~the a~~ contact window of the transparent conducting electrode;
processing ~~the a~~ third masking process for defining a source/drain, and depositing ~~the a~~ second metal wiring layer;
etching the poly-Si layer, and channeling the first ~~metal-wire~~ metal wiring layer and the second ~~metal-wire~~ metal wiring layer; and
processing deposition to form a passivation layer, and disclosing the parts of the transparent conducting electrode.

Claim 2 (Currently amended): The method of manufacturing TFT-LCD array panel according to claim 1, wherein said transparent conducting metal layer can be is made of ITO or IZO.

Claim 3 (Currently amended): The method of manufacturing TFT-LCD array panel according to claim 1, wherein said first ~~metal-wire~~ can be metal wiring layer is made of Al, Cu, Ag, Mo, Cr, Ti, W, or other alloy materials.

Claim 4 (Currently amended): The method of manufacturing TFT-LCD array panel according to claim 1, wherein the ~~deposition process can be against of multi-layer materials and structural~~

~~layers induced from metal materials such as diffusion, and adhesion before the step of forming the first metal wire~~ first metal wiring layer is a multi-layer metal wiring layer.

Claim 5 (Currently amended): The method of forming TFT-LCD array panel according to claim 1, wherein said second metal wires wiring layer is made of can be Al, Cu, Ag, Mo, Cr, Ti, or W as well as low-resistance metals, other alloy materials, or the induced material such as diffusion, and adhesion with multi-layer structure of the metal material.

Claim 6 (Currently amended): The method of forming TFT-LCD array panel according to claim 1, wherein the first masking process, the second masking process, and the third masking process, and the a fourth masking processing can include lithography etching method.

Claim 7 (Currently amended): The method of manufacturing a TFT-LCD array panel according to claim 1, wherein the deposition method of the A-Si layer, the transparent conducting layer, or gate electrode can use uses PVD, Low pressure CVD, or plasma enhanced CVD to implement.

Claim 8 (Currently amended): The method of manufacturing a TFT-LCD array panel according to claim 1, wherein said method forming for the first metal wiring layer can be a selective deposition method, and the selective deposition method uses the a selective conducting wiring layout to deposit the metal on the right position.

Claim 9 (Canceled)

Claim 10 (Currently amended): The method of manufacturing a TFT-LCD array panel according to claim 1, wherein the passivation layer can be made of SiO₂, silicon nitride material, or other organic materials.

Claim 11 (New): The method of forming TFT-LCD array panel according to claim 1, wherein said second metal wiring layer is made of alloy material.

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Claim 12 (New): The method of forming TFT-LCD array panel according to claim 1, wherein said second metal wiring layer is made of alloys of Al, Cu, Ag, Mo, Cr, Ti, or W.

Claim 13 (New): The method of forming TFT-LCD array panel according to claim 1, wherein said second metal wiring layer is made of low resistance materials.

Claim 14 (New): The method of forming TFT-LCD array panel according to claim 1, wherein said second metal wiring layer is a multilayer structure.

Claim 15 (New): The method of forming TFT-LCD array panel according to claim 1, wherein said second metal wiring layer is a multilayer structure comprising Al, Cu, Ag, Mo, Cr, Ti, or W.